风光欣技术资料

C1959

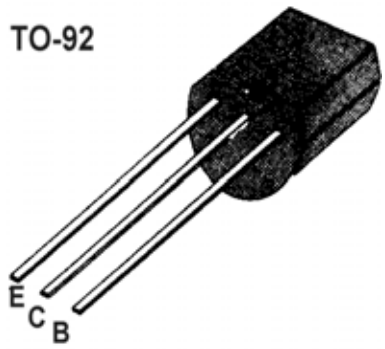
—NPN silicon —

■■APPLICATION：Audio Frequency Low Power Amplifier Applications,

Driver Stage Amplifier Applications, Switching Applications

■■MAXIMUM RATINGS（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	500	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■ELECTRICAL CHARACTERISTICS（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	70		400		V_{CE}= 1V，Ic= 100mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 35V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	35			V	Ic= 0.02mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 0.02mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.25	V	Ic= 100mA，I_B= 10mA
Gain bandwidth product	f_T	120			MHz	Ic= 20mA，V_{CE}= 6V
Common Base Output Capacitance	Cob			7	PF	V_{CB}= 6V，I_E=0，f = 1MHz

■■h_{FE} Classification

Classification	O	Y	GR
h_{FE}	70~140	120~240	200~400